

EAST - interference search

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L5	41	((cd near6 laser) and (dvd near6 laser)).clm.	US-PGPUB	OR	ON	2006/02/02 14:33
L6	229	((laser) and ((buried or burying or enclosed or covered) near ridge or rib)).clm.	US-PGPUB	OR	ON	2006/02/02 14:34
L7	13	((laser) and ((buried or burying or enclosed or covered) near ridge or rib) and (current near blocking or gaas or gallium near arsenide or ingaasp or ingaas or ingap or semiconductor or semiconducting) near6 (burying or buried or bury or wall or sidewall or side or edge)).clm.	US-PGPUB	OR	ON	2006/02/02 14:36
L8	2	((laser) and ((buried or burying or enclosed or covered) near ridge or rib) and (real or gain) near (guided or guide)).clm.	US-PGPUB	OR	ON	2006/02/02 14:37
L9	12	((laser) and (real or gain) near (guided or guide) and (loss or lossy or index or complex or imaginary or attenuated or attenuation) near (guide or guided)).clm.	US-PGPUB	OR	ON	2006/02/02 14:39
L10	2	((laser) and (real or gain) near (guided or guide) and (buried or burying or sidewall or side or edge or wall) same (sin or sio or silicon adj nitride or silicon adj oxide or silicon adj dioxide or sion or oxynitride or dielectric) same (semiconductor or gaas or ga near as or ingaas or gaasp or ingaasp)).clm.	US-PGPUB	OR	ON	2006/02/02 14:40
L11	23	((laser) and (ridge or rib or waveguide or guide) same (buried or burying or sidewall or side or edge or wall) same (sin or sio or silicon adj nitride or silicon adj oxide or silicon adj dioxide or sion or oxynitride or dielectric) same (semiconductor or gaas or ga near as or ingaas or gaasp or ingaasp)).clm.	US-PGPUB	OR	ON	2006/02/02 14:40

EAST - search notes

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L15	21	h01s005/223.ipc. and (buried or burying or enclosed or surrounded) near3 (ridge or rib or waveguide or guide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:29
L14	9	h01s005/223.ipc. and (buried or burying or real or gain or index or loss or covered or sidewall or side or wall or edge) near8 (gallium near arsenide or gaas or ga near as or semiconductor or semiconducting) near8 (dielectric or insulator or insulating or sin or silicon adj nitride or silicon adj oxide or silicon adj dioxide or sio or oxynitride or sion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:28
L13	8	h01s005/223.ipc. and (buried or burying or real or gain or index or loss or covered or sidewall or side or wall or edge) near8 (gallium near arsenide or gaas or ga near as or semiconductor or semiconducting) near8 (dielectric or insulator or insulating or sin or silicon adj nitride or silicon adj oxide or silicon adj dioxide or sio or oxynitride or sion)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:24
L12	749	h01s005/223.ipc.	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:21
L6	804	257/14.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:18
L7	428	257/14.ccls. and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:18
L5	50	372/50.121.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:17
S57	562	372/23.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 13:04
S56	68	(laser) near4 (ridge or rib) near6 (real or gain) near4 (guide or guided or waveguide or guiding or waveguiding)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 11:33
S55	68	(laser) near4 (ridge or rib) near6 (real or gain) near4 (guide or guided or waveguide or guiding or waveguiding)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 11:26
S54	12	(laser) near4 (ridge or rib) near10 (clad or cladding or burying or buried or enclosing or sidewall or wall or overlying or upon or top or "adjacent" or abutting) near4 (dielectric or sin or silicon near nitride or sio or silicon near oxide or silicon near dioxide or oxynitride or sion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 11:25
S53	393	257/89.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 11:22

S51	885	257/88.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 11:18
S52	326	257/88.ccls. and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 11:12
S50	344	257/15.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 11:11
S49	389	257/13.ccls. and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 11:05
S48	603	257/13.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 10:46
S47	105	(monolithic or integral or integrated or unitary) near4 (laser) near6 (dual or multi or multiple or several or two or plural) near4 (wavelength or lambda or frequency) and (gain or complex or imaginary or gaining or real or index or loss or lossy) near4 (waveguide\$3 or guide)	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/02 10:39
S46	359	(monolithic or integral or integrated or unitary) near4 (laser) near6 (dual or multi or multiple or several or two or plural) near4 (wavelength or lambda or frequency)	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/02 10:11
S45	62	(cd or compact near disc) near6 laser and (guide or waveguide) near6 (real or gain) and (gaas or algaas or ga near as or gallium near arsenide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 10:07
S44	198	(cd or compact near disc) near8 (dvd or digital near versatile near disc) near6 laser and (gaas or algaas or ga near as or gallium near arsenide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 09:52
S43	44	(gaas or algaas or ingaas or ga adj as or gallium adj arsenide) near8 laser same (buried or burying or covered or embedded or embedding) near4 (rib or ridge) and (loss or gain or normal or complex or index or indexed) near2 (guide or waveguide or guiding)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 09:47
S42	185	(gaas or ga adj as or gallium near arsenide) and (multi or multiple or plural or plurality or second or secondary or two) near2 (wavelength or lambda) and (loss or lossy) near2 (guide or waveguide or section or area or length or region) and (gain or gaining or multiplication) near2 (guide or waveguide or section or area or length or region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/02 09:33
S41	43	(laser or cd) and (ridge) near4 (burying or buried or cladding) near8 (silicon adj nitride or sin or sio or silicon adj oxide or silicon adj dioxide or dielectric or oxynitride)	US-PGPUB; USPAT	OR	ON	2006/02/02 09:24

S40	25	(US-20010048111-\$ or US-20020008242-\$ or US-20020185643-\$ or US-20030021320-\$ or US-20030043874-\$ or US-20030043875-\$ or US-20030133484-\$ or US-20030152123-\$ or US-20050030997-\$ or US-20050100060-\$ or US-20050117616-\$).did. or (US-5701322-\$ or US-5898722-\$ or US-5982799-\$ or US-6287884-\$ or US-6358764-\$ or US-6472680-\$ or US-6480456-\$ or US-6542528-\$ or US-6614821-\$ or US-6618420-\$ or US-6643310-\$ or US-6738402-\$ or US-6757311-\$ or US-6900069-\$).did.	US-PGPUB; USPAT	OR	ON	2006/02/02 09:23
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